



## SOT-23 Plastic-Encapsulate Transistors

**BC856A, B** TRANSISTOR (PNP)

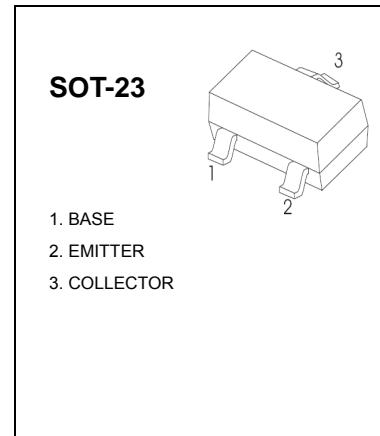
**BC857A, B,C**

**BC858A, B,C**

### FEATURES

- Ideally suited for automatic insertion
- For Switching and AF Amplifier Applications

**MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**



Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage		
	BC856	-80	V
	BC857	-50	
	BC858	-30	
V <sub>CEO</sub>	Collector-Emitter Voltage		
	BC856	-65	V
	BC857	-45	
	BC858	-30	
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current –Continuous	-0.1	A
P <sub>C</sub>	Collector Power Dissipation	200	mW
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-65-150	°C

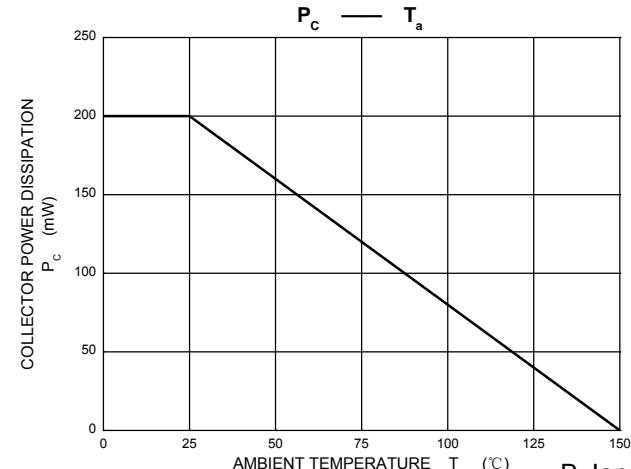
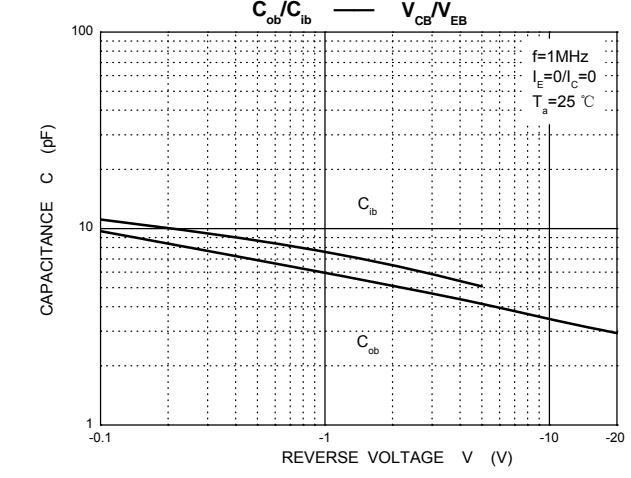
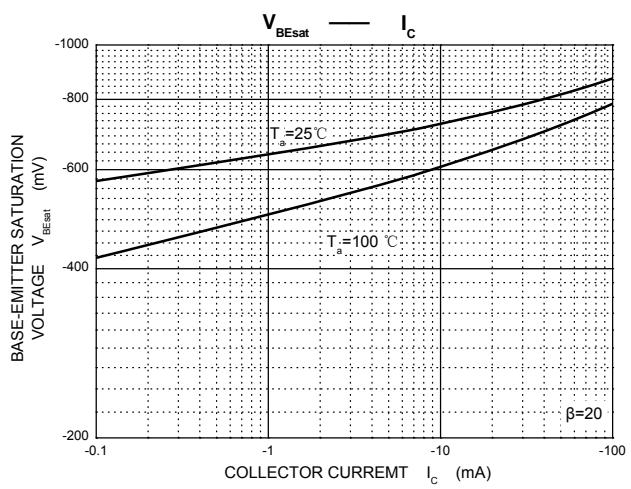
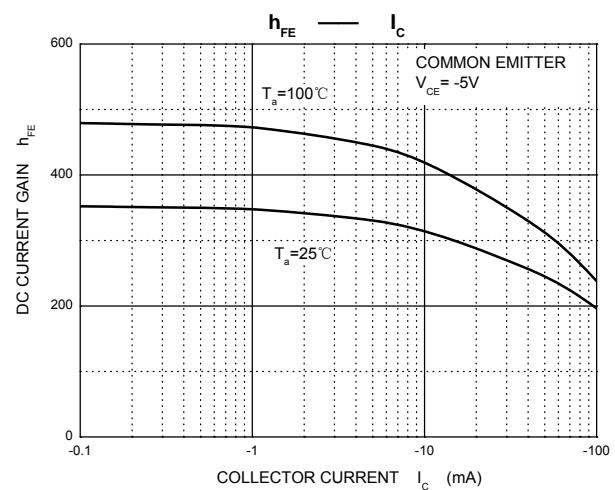
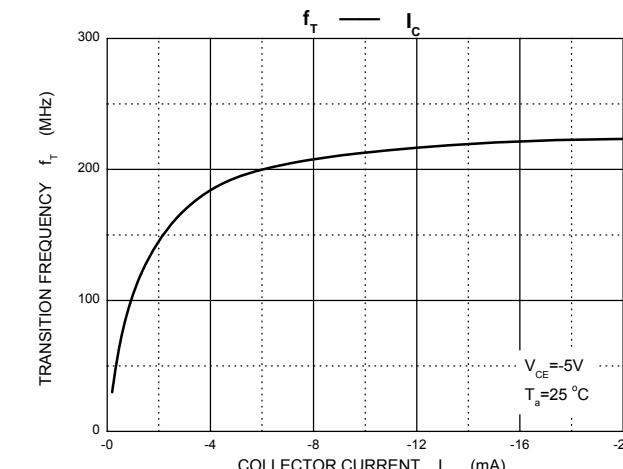
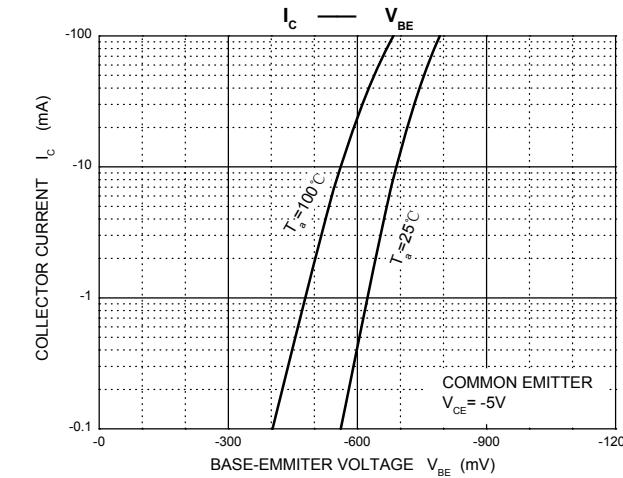
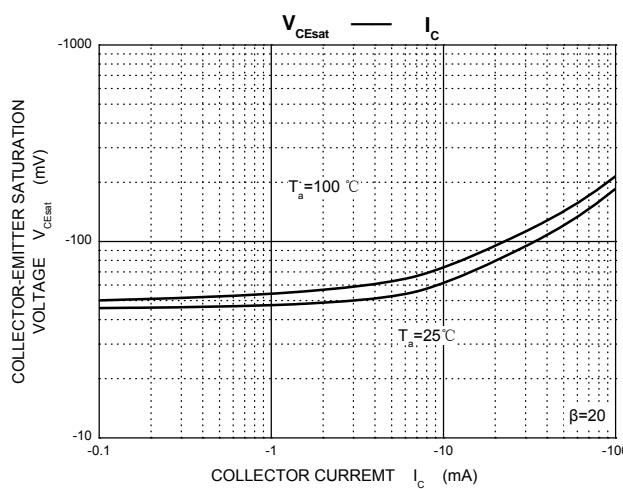
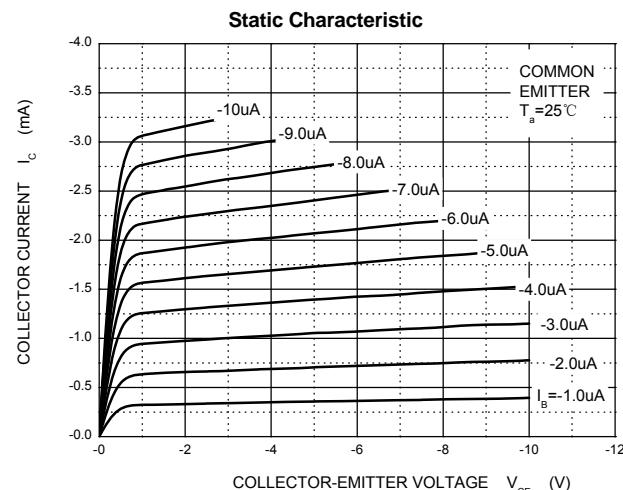
### DEVICE MARKING

BC856A=3A; BC856B=3B;  
BC857A=3E;BC857B=3F;BC857C=3G;  
BC858A=3J; BC858B=3K; BC858C=3L

**ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$  unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage <b>BC856</b> <b>BC857</b> <b>BC858</b>	$V_{CBO}$	$I_C = -10\mu\text{A}, I_E = 0$	-80		
			-50		V
			-30		
Collector-emitter breakdown voltage <b>BC856</b> <b>BC857</b> <b>BC858</b>	$V_{CEO}$	$I_C = -10\text{mA}, I_B = 0$	-65		
			-45		V
			-30		
Emitter-base breakdown voltage	$V_{EBO}$	$I_E = -1\mu\text{A}, I_C = 0$	-5		V
Collector cut-off current <b>BC856</b> <b>BC857</b> <b>BC858</b>	$I_{CBO}$	$V_{CB} = -70\text{ V}, I_E = 0$ $V_{CB} = -45\text{ V}, I_E = 0$ $V_{CB} = -25\text{ V}, I_E = 0$		-0.1	$\mu\text{A}$
Collector cut-off current <b>BC856</b> <b>BC857</b> <b>BC858</b>	$I_{CEO}$	$V_{CE} = -60\text{ V}, I_B = 0$ $V_{CE} = -40\text{ V}, I_B = 0$ $V_{CE} = -25\text{ V}, I_B = 0$		-0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5\text{ V}, I_C = 0$		-0.1	$\mu\text{A}$
DC current gain <b>BC856A, 857A,858A</b> <b>BC856B, 857B,858B</b> <b>BC857C,BC858C</b>	$h_{FE}$	$V_{CE} = -5\text{V}, I_C = -2\text{mA}$	125	250	
			220	475	
			420	800	
Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	$I_C = -100\text{mA}, I_B = -5\text{ mA}$		-0.5	V
Base-emitter saturation voltage	$V_{BE(\text{sat})}$	$I_C = -100\text{mA}, I_B = -5\text{mA}$		-1.1	V
Transition frequency	$f_T$	$V_{CE} = -5\text{ V}, I_C = -10\text{mA}$ $f = 100\text{MHz}$	100		MHz
Collector capacitance	$C_{ob}$	$V_{CB} = -10\text{V}, f = 1\text{MHz}$		4.5	pF

# Typical Characteristics BC856/BC857/BC858



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